Electric Field Effects in Ultrathin $YBa_2Cu_3O_{7-\delta}$ Films

Yoshichika Bando and Takahito Terashima

Charging effects on transport properties of ultrathin $YBa_2Cu_3O_{7-\delta}$ (YBCO) films are measured using FET-like junctions of YBCO in thickness ranging from 1 to 10 unit cell thicknesses (UCT). An electric(E-) field experiment without magnetic field finds that the changes of Kosterlitz-Thouless transition temperature is observed as a function of applied E-field. The changes of superconducting properties are linearly correlated to those of the normal resistance, namely, the induced areal carrier densities.

Keywords: High-T_C superconductivity/ $YBa_2Cu_3O_{7-\delta}$/ Ultrathin film/ Electric field effect

Electric (E-) field effects in superconductors have attracted much attentions from the interest in fundamental physics as well as the device applications. By using an E-field effect junction, we could examine an effect of the carrier density on superconductivity without any reconstruction of sample structure. The change of superconducting transition temperature T_C by E-field have observed for the first time for the thin films of conventional superconductors of Sn and In. Recent works on the E-field effects are mainly devoted to high temperature superconductors (HTSC) since the effects on superconductivity are expected to be large because of the low carrier density n and the short coherence length of HTSC. Here we will report the E-field effects in ultrathin $YBa_2Cu_3O_{7-\delta}$ (YBCO) films [1,2].

Figure 1 depicts the top view of a 3-terminal junction used in the E-field effect experiment. *C*-axis-oriented YBCO films with thicknesses from 1 to 10 unit-cell-thickness (UCT) were prepared onto a (100) surface of $SrTiO_3$(STO) by using an activated-reactive evaporation technique. A buffer layer of several UCT nonsuperconducting $PrBa_2Cu_3O_{7-\delta}$(PBCO) was first prepared onto a STO (100) substrate heated up to 680 ˚C, and then a YBCO film was grown onto the buffer layer of PBCO. After deposition of a 3 nm capping layer of STO on YBCO film, the film was cooled down to room temperature in an oxygen atmosphere of 0.01 MPa. After exposure to air, a masking plate was set up to open a window wider than the sample area of YBCO for STO deposition. A thick dielectric STO film (120 nm) was deposited onto the capping STO layer at 690˚C. Finally a gate electrode of thin Pt film (40nm) was prepared in a separate evaporator with a lead wire attached. The distribution of applied E-field in the YBCO film was uniform over the sample. An areal charge density ΔN induced in the junction area S (0.51cm^2) of the YBCO film was evaluated by $\Delta N = CV_g/eS$ from an applied gate voltage V_g and a capacitance C that was almost independent of temperature T within an error of 20% in the temperature range of this experiment between 4K and 100K, where S is the surface area of the capacitor and e is the unit charge. The

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Scope of research

Syntheses of oxide thin films by reactive evaporation and ceramics by solid state reaction and their characterizations are studied. The main subjects are: preparation and characterization of ultrathin films of high-T_c superconductors: investigation of growth mechanism of thin films by in situ reflection high-energy electron diffraction: phase diagram of Bi_2O_3-SrO-CaO-CuO system: growth and characterization of single crystals of Bi-Sr-Ca-Cu-O system: preparation and observation of dielectric properties of ferroelectric thin films: preparation and characterization of metallic and ferromagnetic $SrRuO_3$ thin films: scanning tunneling microscope observation of surface structures and electronic states of metallic oxide thin films

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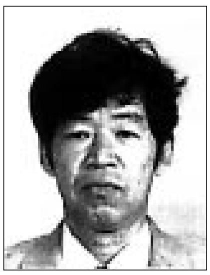

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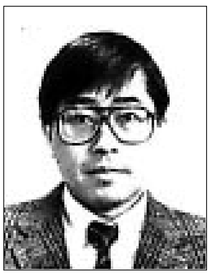

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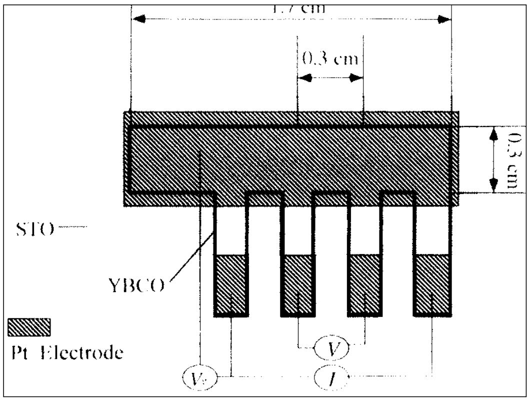

Figure 1. Top view of a FET-like junction.

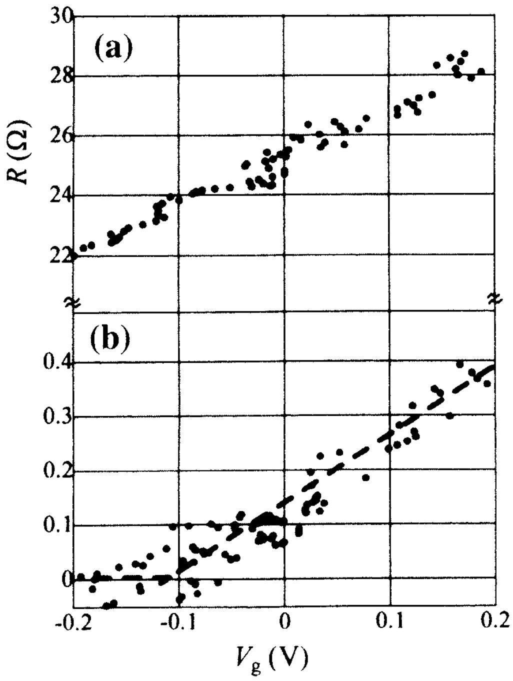

Figure 2. Change in R as a function of V_g for a 2UCT YBCO film at two representative fixed temperatures. (a) is for T = 45K and (b) for T = 35K, respectively.

dielectric constant of STO film was evaluated from the capacitance measurement as ε_e~2000 and the induced areal carrier density ΔN can be calculated via $\Delta N = \varepsilon_e \varepsilon_0 V_g/de$ = $9.22\times10^{13} V_g$(/cm^2) with d = 120nm, where ε_0 is the dielectric constant in vacuum.

E-field effects on resistance for 2 UCT (2.4nm)YBCO film are shown in Figs. 2(a) and (b) for representative fixed temperatures, that is, (a) is in the transition region of high resistance state at 45 K and (b) immediately above the onset temperature of R, respectively, where we applied a gate voltage to a Pt electrode. In Fig.2(a) , resistance R changes linearly with V_g across V_g = 0. For a negative V_g, R is lowered with decreasing V_g, and it is enhanced for an opposite polarization of V_g. On the other hand, in Fig. 2(b), R changes

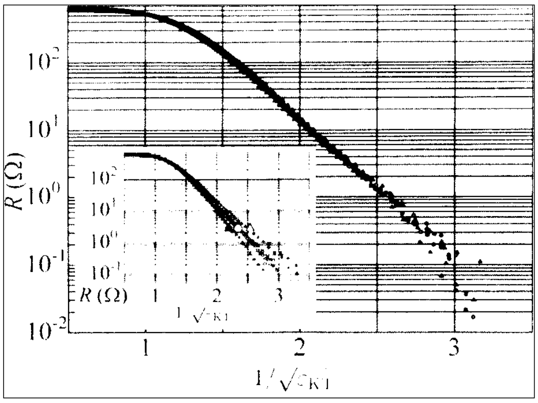

Figure 3. Temperature dependence of the resistance scaled in terms of ε_{KT} for a 2UCT YBCO film under zero magnetic field. The inset shows these in terms of ε_{KT0}. Symbols denote (O) V_g = 0, (Δ) V_g = 0.29V and (▲) V_g = -0.29V, respectively.

with V_g in a nonlinear fashion, that is, it approaches zero at a certain negative V_g and remains zero for a large negative V_g within an experimental error. This indicates that the onset temperature of zero resistance is altered by the applied E-field.

We analyzed the superconducting transition of ultrathin YBCO films by using the theory of Kosterlitz-Thouless (KT) transition. The superconducting part σ_S of the sheet conductance σ for the KT transition ig given by

$$\sigma_S = \sigma_N \exp(2(b\varepsilon_C/\varepsilon_{KT})^{1/2}) \qquad (1)$$

where σ_N and b are unknown parameters, $\varepsilon_C = (T_{mf}-T_{KT})/T_{KT}$, $\varepsilon_{KT} = (T-T_{KT})/T_{KT}$, T_{KT} is the transition tempertature of the KT transition, and T_{mf} is that of the mean-field transition, respectively. To evaluate T_{KT} we treated σ_N, $b\varepsilon_c$ and T_{KT} as fitting parameters and then the temperature was scaled to ε_{KT}. We obtain for T_{KT} 33.39K, 34.09K and 34.79K for V_g = +0.29V, 0V and -0.29V, respectively.

In Fig. 3, resistance curves under applied E-fields V_g = +0.29 V and V_g =0 are shown in respective scaling temperatures $1/(\varepsilon_{KT})^{1/2}$ based on eq. (1) where T_{KT} is chosen for each V_g. For scaling, R is shown against the scaling temperature $1/(\varepsilon_{KT0})^{1/2}$ for a fixed T_{KT} of V_g = 0 in the inset of Fig. 3. Here, the curves for V_g = +0.29V are separated by a straight line for V_g = 0 and deviate from each other at low temperatures. In contrast to this, they collapse into a unified function when scaling temperatures $1/(\varepsilon_{KT})^{1/2}$ are used for respective T_{KT}´s for each V_g.

We compare the E-field effects on T_{KT} with those on R_n and find that $\Delta T_{KT}/T_{KT}$ is proportional to $\Delta R/R_{n0}$ for various applied E fields. E-field effects study for other systems is in progress.

References

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